TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process)

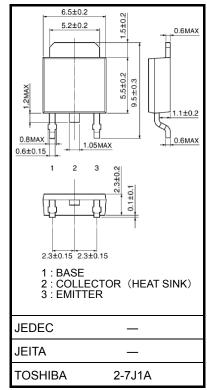
# 2SC6076

## Power Amplifier Applications Power Switching Applications

Low collector saturation voltage: VCE (sat) = 0.5 V (max)  $\rm (IC$  = 1A) High-speed switching:  $t_{stg}$  = 0.4  $\mu s$  (typ)

## Absolute Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit	
Collector-base voltage	V <sub>CBO</sub>	160	V	
Collector-emitter voltage	V <sub>CEX</sub>	160	V	
Collector-emitter voltage	V <sub>CEO</sub>	80	V	
Emitter-base voltage	V <sub>EBO</sub>	9	V	
Collector current	DC	Ι <sub>C</sub>	3	А
	Pulse	I <sub>CP</sub>	5	А
Base current	Ι <sub>Β</sub>	1.5	А	
Collector power dissipation	Tc = 25°C	PC	10	W
Junction temperature	Tj	150	°C	
Storage temperature range		T <sub>stg</sub>	-55~150	°C



Weight:0.36g(typ)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in

temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

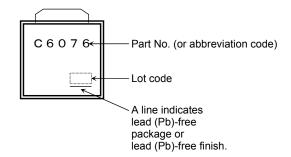
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Unit: mm

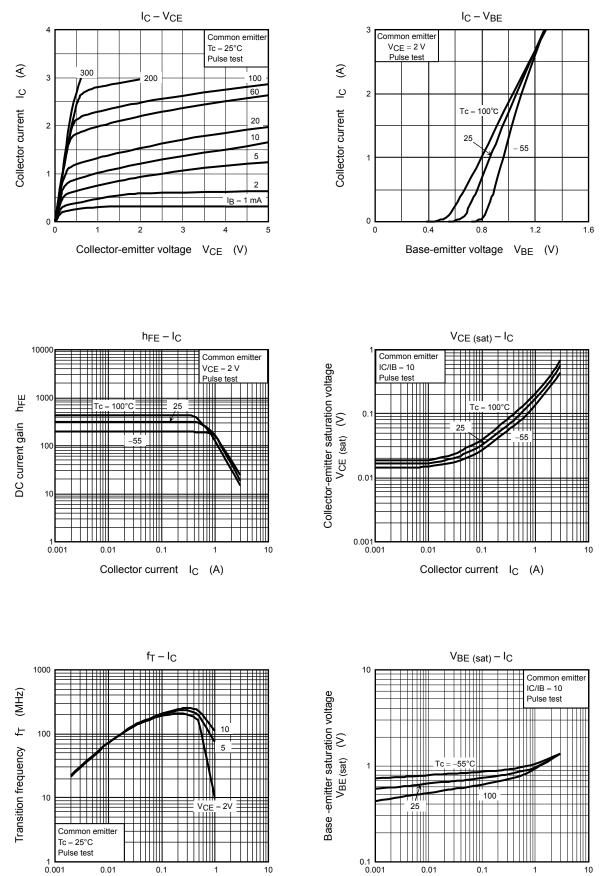
Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Conditions	Min	Тур.	Max	Unit
Collector cut-off current		I <sub>CBO</sub>	V <sub>CB</sub> = 160 V, I <sub>E</sub> = 0	_	_	1.0	μA
Emitter cut-off current		I <sub>EBO</sub>	V <sub>EB</sub> = 9 V, I <sub>C</sub> = 0	-	_	1.0	μA
Collector-emitter breakdown voltage		V (BR) CEO	I <sub>C</sub> = 10 mA, I <sub>B</sub> = 0	80	_	_	V
DC current gain		h <sub>FE (1)</sub>	V <sub>CE</sub> = 2 V, I <sub>C</sub> = 1 mA	150	_	_	
		h <sub>FE (2)</sub>	V <sub>CE</sub> = 2 V, I <sub>C</sub> = 0.5 A	180	_	450	
		h <sub>FE (3)</sub>	V <sub>CE</sub> = 2 V, I <sub>C</sub> = 1 A	100	_	_	
Collector emitter saturation voltage		V <sub>CE (sat) (1)</sub>	I <sub>C</sub> = 0.5 A, I <sub>B</sub> = 50 mA	_	_	0.3	V
		V <sub>CE</sub> (sat) (2)	I <sub>C</sub> = 1 A, I <sub>B</sub> = 100 mA	_	_	0.5	V
Base-emitter saturation voltage		V <sub>BE (sat)</sub>	I <sub>C</sub> = 1 A, I <sub>B</sub> = 100 mA	_	_	1.5	V
Transition frequency		f <sub>T</sub>	V <sub>CE</sub> = 2 V, I <sub>C</sub> = 0.5 A		150	_	MHZ
Collector output capacitance		C <sub>ob</sub>	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0,f = 1MH <sub>Z</sub>	_	14	_	pF
Switching time	Rise time	tr	$20 \ \mu s$ $Input$ $Input$ $IB1$ $IB1$ $V_{CC} = 24 \ V$ $IB1 = -IB2 = 100 \ mA$ Duty cycle $\leq 1\%$	_	0.05	_	
	Storage time	t <sub>stg</sub>		_	0.4	_	μS
	Fall time	t <sub>f</sub>		_	0.15	_	

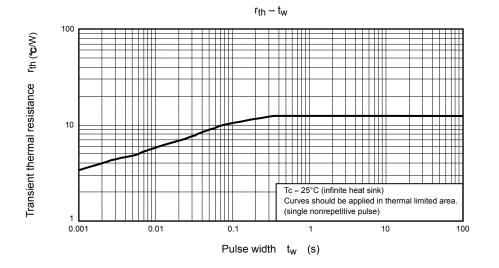
# Marking

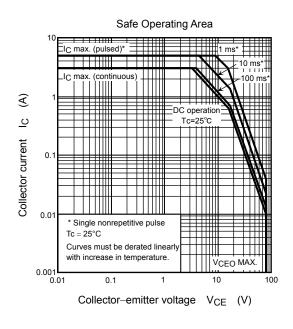


# **TOSHIBA**



Collector current I<sub>C</sub> (A)





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